

Abstract of the Disclosure

The present invention provides a method for fabricating a semiconductor device capable of improving a gap-fill property of a conductive wire. To achieve this effect, the inventive method includes the steps of: forming a plurality of conductive patterns on a substrate in the first region and the second region, wherein each of the conductive patterns includes sequentially stacked layers of a conductive layer and a hard mask; removing the hard mask in the second region to expose the conductive layer; forming a diffusion barrier layer on the exposed conductive layer; depositing an insulation layer on the entire resulting substrate structure in the first region and the second region; selectively etching the insulation layer in the second region to form an opening exposing the diffusion barrier layer; and forming a conductive wire electrically connected to the diffusion barrier layer through the opening.